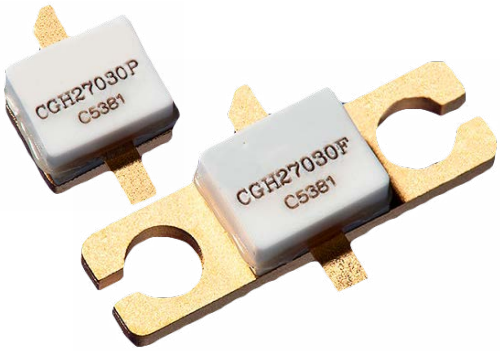
CGH27030

30 W, 28 V, GaN HEMT for Linear Communications ranging from VHF to 3 GHz



Package Types: 440196 and 440166
PN's: CGH27030P and CGH27030F

Description

The CGH27030 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH27030 ideal for VHF, Comms, 3G, 4G, LTE, 2.3-2.9 GHz WiMAX and BWA amplifier applications. The unmatched transistor is available in both screwdown, flange and solder-down, pill packages.

Typical Performance Over 2.3-2.7GHz (T_C = 25˚C) of Demonstration Amplifier

Parameter	2.3 GHz	2.4 GHz	2.5 GHz	2.6 GHz	2.7 GHz	Unit
Small Signal Gain	15.6	15.5	15.3	15.1	15.2	dB
EVM at P_{AVE} = 36 dBm	1.73	1.85	1.85	1.77	1.43	%
Drain Efficiency at 36 dBm	28.1	28.7	28.9	27.9	27.5	%
Input Return Loss	6.6	6.2	6.0	6.1	7.0	dB

Notes:
[1] Measured in the CGH27030F-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF.

Features

- VHF - 3.0 GHz Operation
- 30 W Peak Power Capability
- 15 dB Small Signal Gain
- 4.0 W P_{AVE} at < 2.0 % EVM
- 28% Drain Efficiency at 4 W Average Power
- WiMAX Fixed Access 802.16-2004 OFDM
- WiMAX Mobile Access 802.16e OFDMA

Large Signal Models Available for ADS and MWO

RoHS compliant

Rev. 4.2, 2022-10-20

Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	120	V	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2		
Power Dissipation	P_{DISS}	14	W	
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Forward Gate Current	I_{GMAX}	4.0	mA	25°C
Maximum Drain Current[1]	I_{DMAX}	3.0	A	
Soldering Temperature[2]	T_S	245	°C	
Screw Torque	τ	40	in-oz	
Thermal Resistance, Junction to Case[3]	$R_{\theta JC}$	4.8	°C/W	85°C
Case Operating Temperature[3]	T_C	-40, +150	°C	

Notes:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering
[3] Measured for the CGH27030F at P_{DISS} = 14 W

Electrical Characteristics (T_C = 25°C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 7.2 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	—	-2.7	—		V_{DS} = 28 V, I_D = 150 A
Saturated Drain Current	I_{DS}	5.8	7.0	—	A	V_{DS} = 6.0 V, V_{GS} = 2 V
Drain-Source Breakdown Voltage	V_{BR}	84	—	—	V_{DC}	V_{GS} = -8 V, I_D = 7.2 mA
RF Characteristics[2, 3] (T_C = 25°C, F_0 = 2.5 GHz unless otherwise noted)						
Small Signal Gain	G_{SS}	12.5	14.5	—	dB	V_{DD} = 28 V, I_{DQ} = 150 mA
Drain Efficiency[4]	η	23.0	28.0	—	%	V_{DD} = 28 V, I_{DQ} = 150 mA, P_{AVE} = 4 W
Error Vector Magnitude	EVM	—	2.0	—		
Output Mismatch Stress	VSWR	—	—	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 150 mA, P_{AVE} = 4.0 W OFDM P_{AVE}
Dynamic Characteristics						
Input Capacitance	C_{GS}	—	9.0	—	pF	V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz
Output Capacitance	C_{DS}	—	2.6	—		
Feedback Capacitance	C_{GD}	—	0.4	—		

Notes:
[1] Measured on wafer prior to packaging
[2] Measured in the CGH27030F-AMP test fixture
[3] Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF
[4] Drain Efficiency = P_{OUT}/P_{DC}
[5] Capacitance values include package parasitics

Typical WiMAX Performance

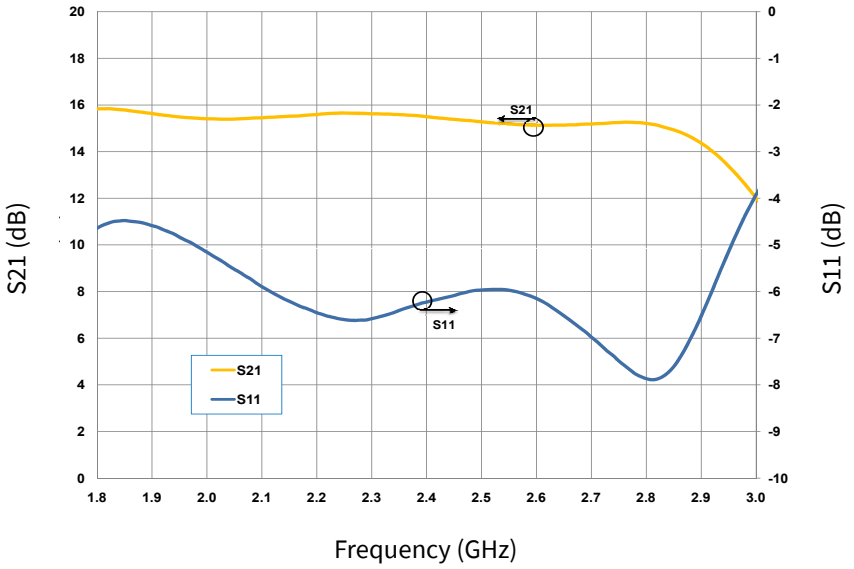


Figure 1. Small Signal S-Parameters vs Frequency measured in CGH27030F-AMP
V_{DD} = 28 V, I_{DQ} = 150 mA

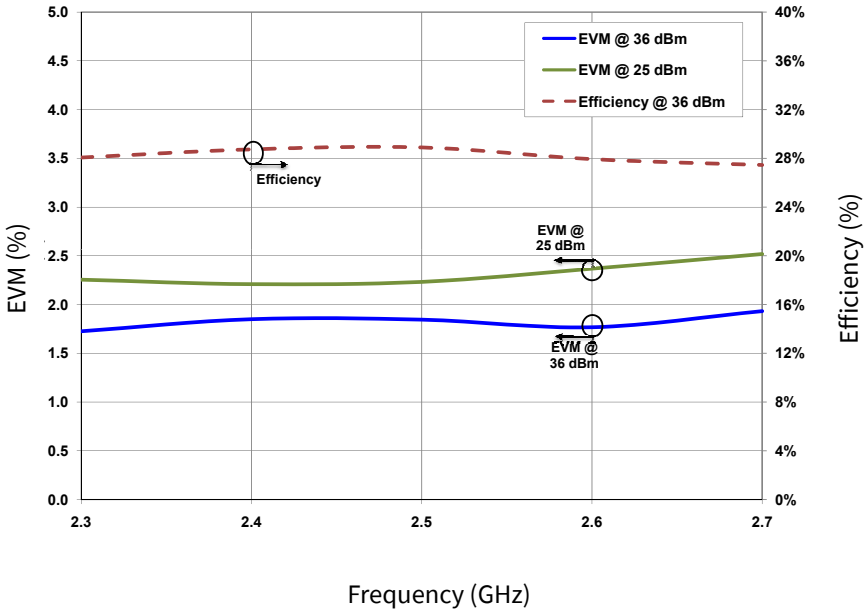


Figure 2. Typical EVM and Efficiency versus Frequency measured in CGH27030F-AMP
V_{DS} = 28 V, I_{DQ} = 150 mA, 802.16-2004 OFDM, PAR = 9.8 dB, P_{AVE} = 5 W

Note:
[1] Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF.

Typical WiMAX Performance

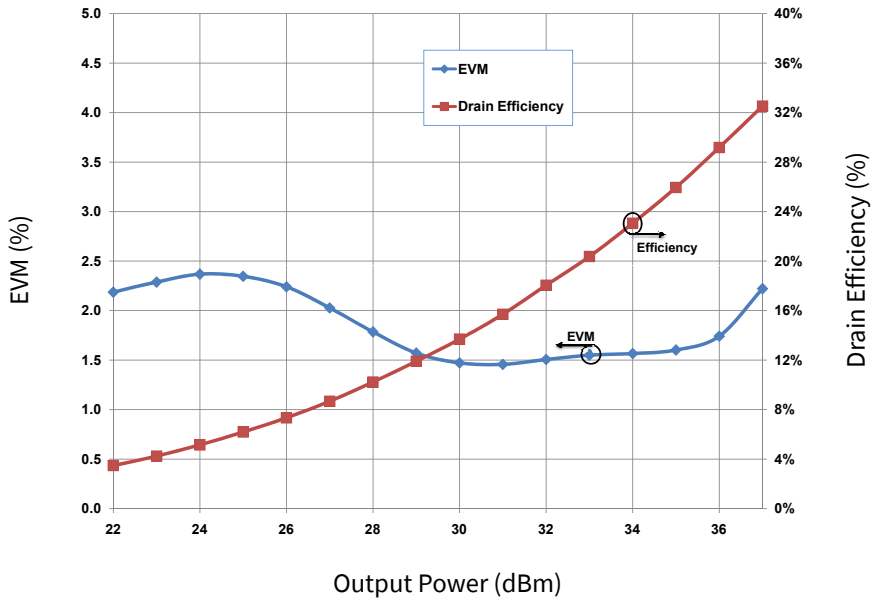


Figure 3. Drain Efficiency and EVM vs Output Power measured in CGH27030F-AMP
V_{DD} = 28 V, I_{DQ} = 150 mA, 802.16-2004 OFDM, PAR = 9.8 dB

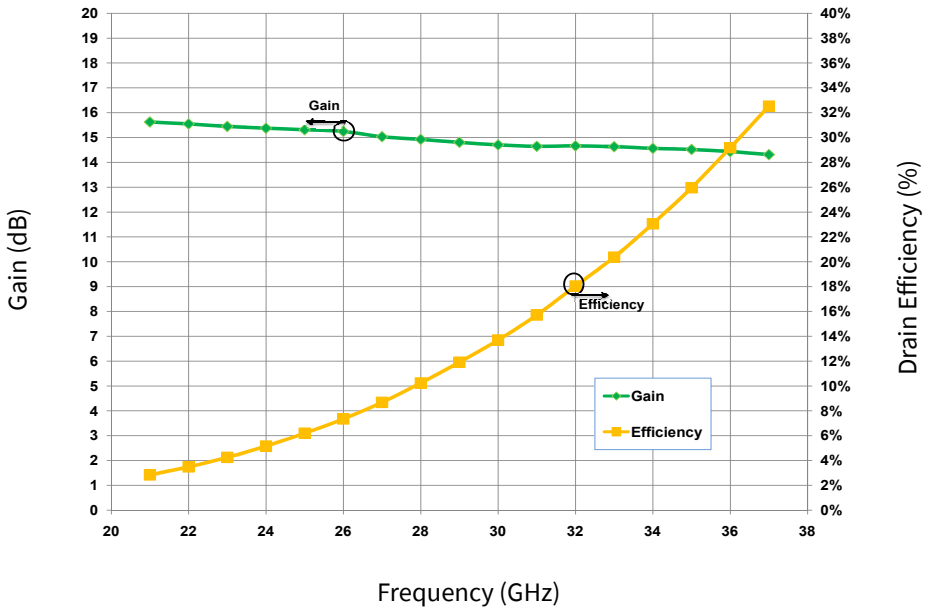


Figure 4. Typical Gain and Efficiency vs Output Power measured in CGH27030F-AMP
V_{DD} = 28 V, I_{DQ} = 150 mA, 802.16-2004 OFDM, PAR = 9.8 dB

Typical Performance Data

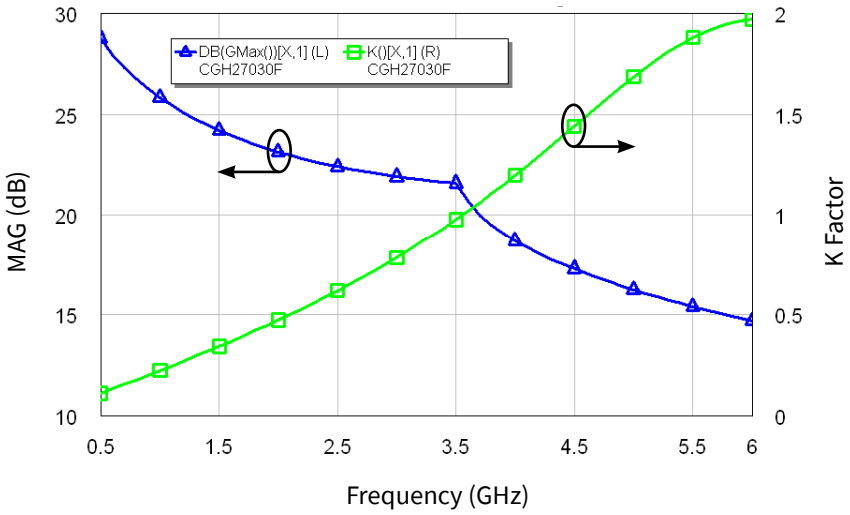


Figure 5. Simulated Maximum Available Gain and K Factor of the CGH27030F
V_{DD} = 28 V, I_{DQ} = 150 mA

Typical Noise Performance

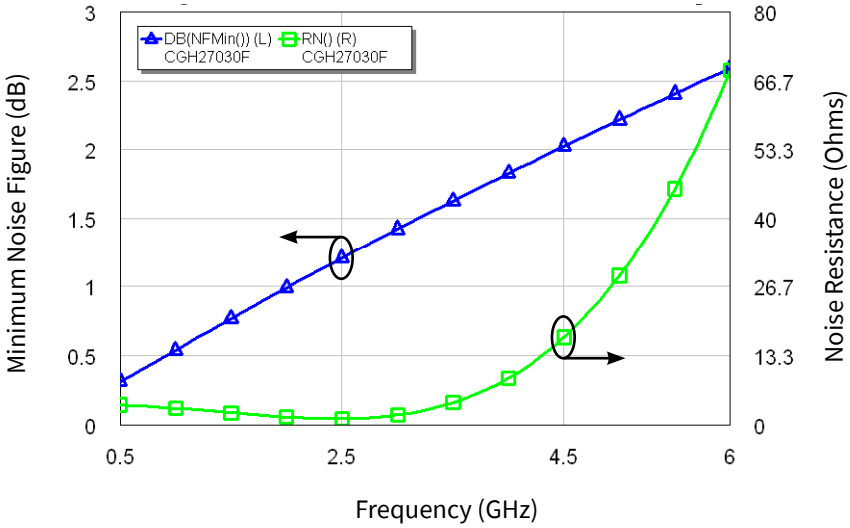
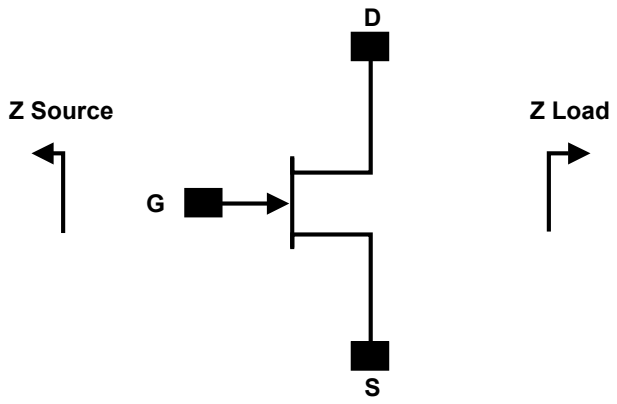


Figure 6. Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH27030
V_{DD} = 28 V, I_{DQ} = 150 mA

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

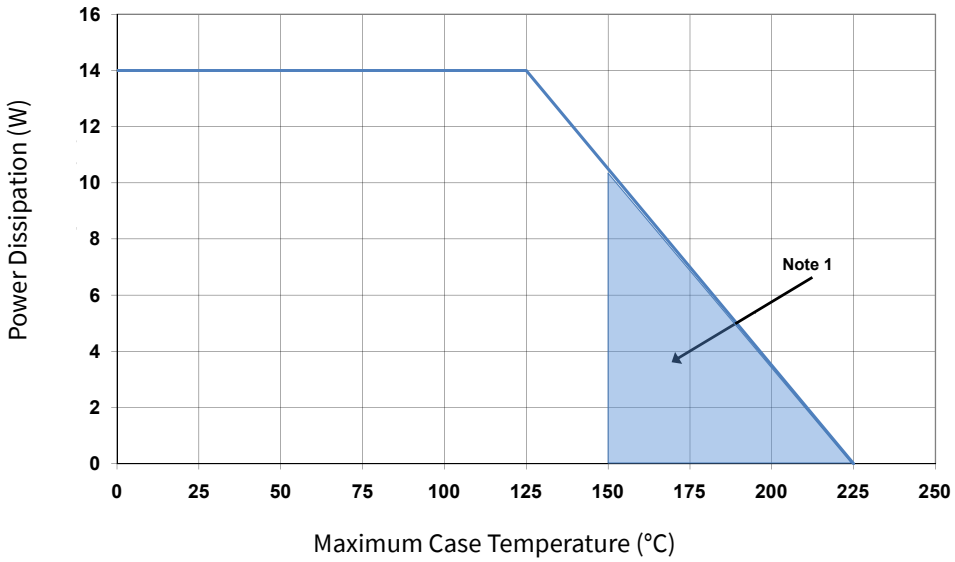
Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
500	7.75 + j15.5	20 + j5.2
1000	3.11 + j5.72	17 + j6.66
1500	2.86 + j1.63	16.8 + j3.2
2500	1.2 - j3.26	9.41 + j3.2
3500	1.31 - j7.3	5.85 - j0.51

Notes:
[1] V_{DD} = 28 V, I_{DQ} = 250mA. In the 440166 package
[2] Optimized for power gain, P_{SAT} and P_{AE}
[3] When using this device at low frequency, series resistors should be used to maintain amplifier stability

CGH27030 Average Power Dissipation De-rating Curve

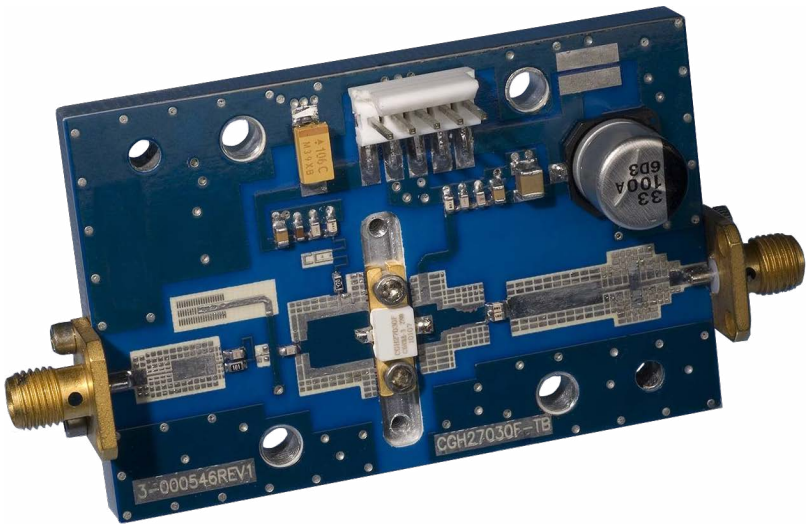


Note:
[1] Area exceeds Maximum Case Operating Temperature (See Page 2)

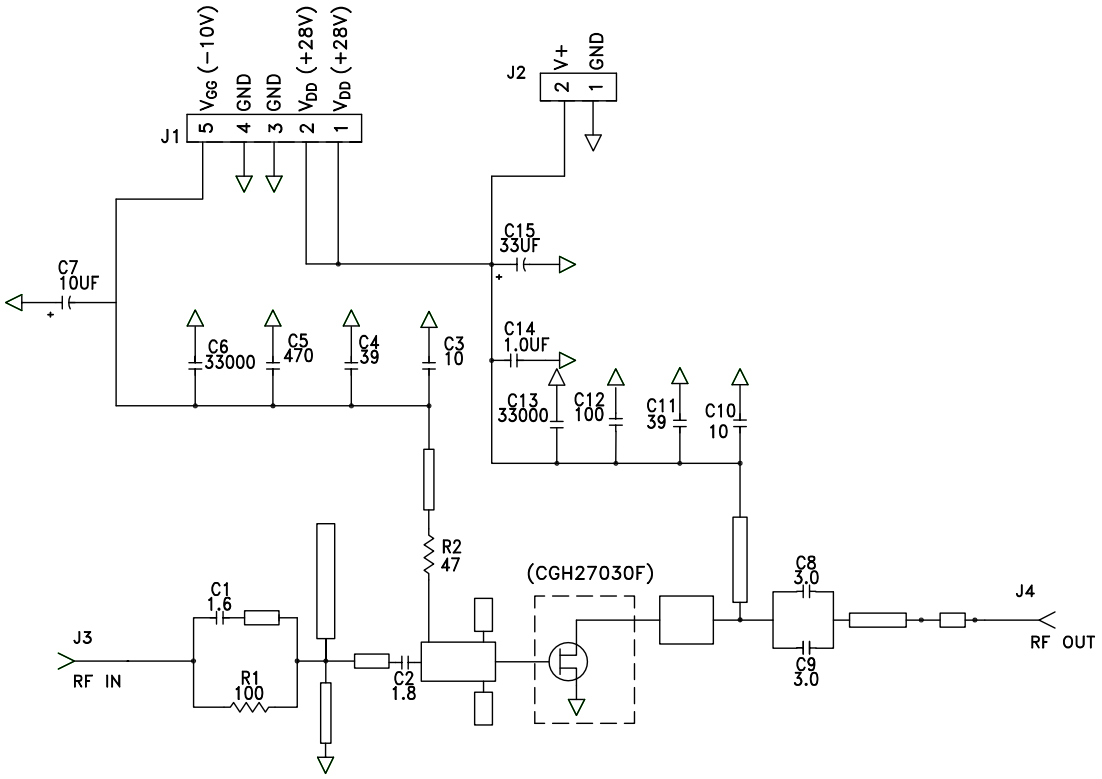
CGH27030F-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 1/16W, 0603, 1%,100 OHMS	1
R2	RES, 1/16W,0603, 1%,47 OHMS	1
C5	CAP, 470pF, 5%,100V, 0603	1
C15	CAP, 33µF, 20%, G CASE	1
C14	CAP, 1.0µF, 100V, 10%, X7R, 1210	1
C7	CAP 10µF, 16V TANTALUM	1
C12	CAP, 100.0pF, +/-5%, 0603	1
C1	CAP, 1.6pF, +/-0.1pF, 0603	1
C2	CAP, 1.8pF, +/-0.1pF, 0603	1
C3, C10	CAP, 10.0pF,+/-5%, 0603	2
C4, C11	CAP, 39pF, +/-5%, 0603	2
C8, C9	CAP, 3.0pF, +/-0.1pF, 0603	2
C6, C13	CAP, 33000pF, 0805,100V, X7R	2
J3, J4	CONN SMA STR PANEL JACK RECP	1
J2	HEADER RT>PLZ.1CEN LK 2 POS	1
J1	J1 HEADER RT>PLZ .1CEN LK 5POS	1
—	PCB, RO4350B, Er = 3.48, h = 20 mil	1
—	CGH27030F	1

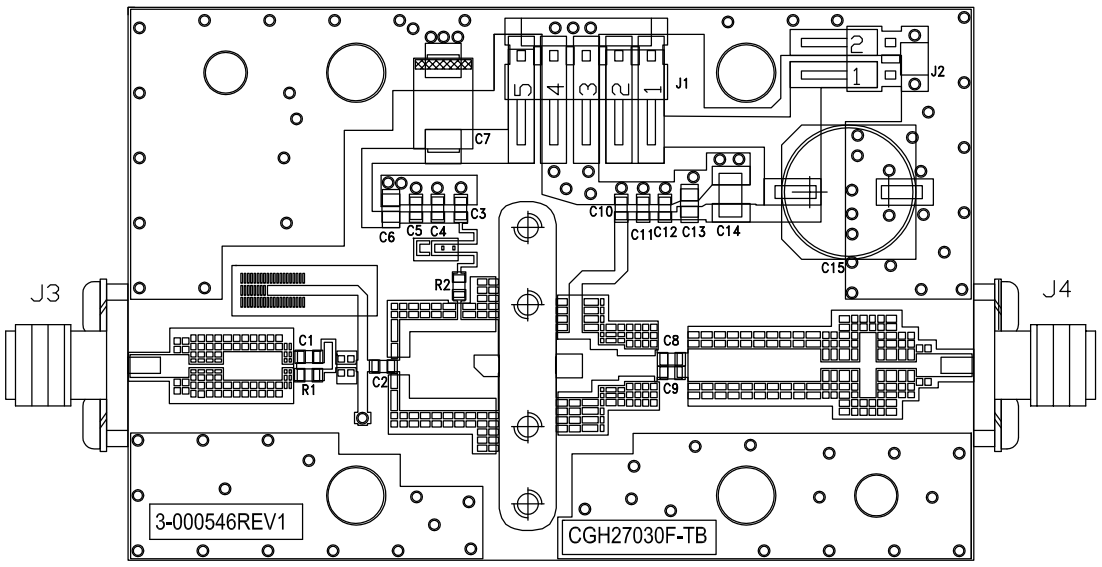
CGH27030F-AMP Demonstration Amplifier Circuit



CGH27030F-AMP Demonstration Amplifier Circuit Schematic



CGH27030F-AMP Demonstration Amplifier Circuit Outline

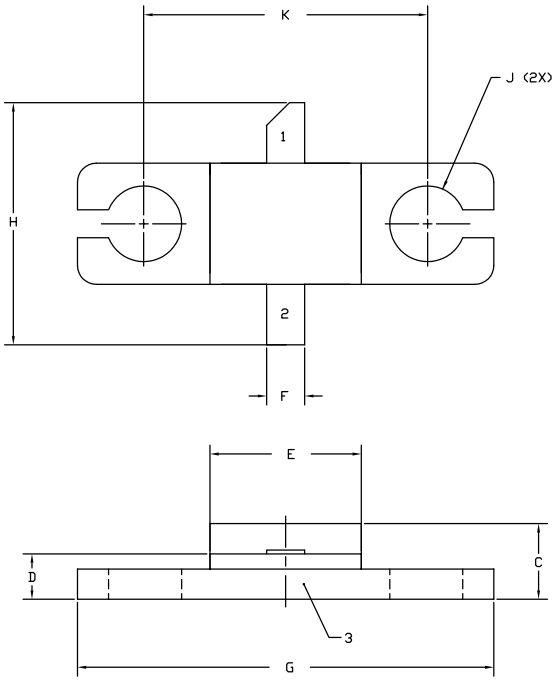


Typical Package S-Parameters for CGH27030
(Small Signal, V_{DS} = 28 V, I_{DQ} = 150 A, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.910	-127.91	18.04	106.46	0.024	20.12	0.314	-103.83
600 MHz	0.904	-137.21	15.52	100.35	0.025	14.75	0.306	-111.67
700 MHz	0.900	-144.50	13.58	95.23	0.025	10.38	0.302	-117.66
800 MHz	0.897	-150.40	12.04	90.78	0.025	6.69	0.302	-122.33
900 MHz	0.895	-155.33	10.80	86.81	0.026	3.48	0.303	-126.06
1.0 GHz	0.894	-159.54	9.78	83.20	0.026	0.63	0.306	-129.12
1.1 GHz	0.893	-163.21	8.93	79.85	0.026	-1.95	0.310	-131.69
1.2 GHz	0.892	-166.46	8.22	76.69	0.025	-4.31	0.315	-133.89
1.3 GHz	0.891	-169.40	7.60	73.70	0.025	-6.51	0.321	-135.84
1.4 GHz	0.891	-172.09	7.07	70.84	0.025	-8.56	0.327	-137.59
1.5 GHz	0.891	-174.57	6.61	68.08	0.025	-10.50	0.334	-139.20
1.6 GHz	0.891	-176.88	6.20	65.41	0.025	-12.34	0.341	-140.70
1.7 GHz	0.891	-179.07	5.84	62.81	0.025	-14.09	0.348	-142.13
1.8 GHz	0.891	178.86	5.52	60.28	0.025	-15.76	0.355	-143.51
1.9 GHz	0.891	176.88	5.23	57.79	0.024	-17.36	0.362	-144.85
2.0 GHz	0.891	174.98	4.96	55.35	0.024	-18.90	0.370	-146.16
2.1 GHz	0.891	173.13	4.73	52.95	0.024	-20.38	0.378	-147.46
2.2 GHz	0.892	171.34	4.51	50.59	0.024	-21.80	0.385	-148.75
2.3 GHz	0.892	169.60	4.32	48.25	0.023	-23.16	0.393	-150.03
2.4 GHz	0.892	167.89	4.14	45.95	0.023	-24.48	0.400	-151.32
2.5 GHz	0.892	166.20	3.97	43.66	0.023	-25.74	0.408	-152.61
2.6 GHz	0.893	164.55	3.82	41.40	0.023	-26.95	0.415	-153.91
2.7 GHz	0.893	162.91	3.68	39.16	0.022	-28.11	0.422	-155.21
2.8 GHz	0.893	161.28	3.54	36.93	0.022	-29.22	0.429	-156.52
2.9 GHz	0.893	159.67	3.42	34.72	0.022	-30.28	0.436	-157.84
3.0 GHz	0.894	158.06	3.31	32.52	0.021	-31.28	0.443	-159.17
3.2 GHz	0.894	154.86	3.10	28.16	0.021	-33.13	0.456	-161.87
3.4 GHz	0.894	151.65	2.92	23.83	0.020	-34.76	0.469	-164.62
3.6 GHz	0.895	148.41	2.77	19.52	0.020	-36.15	0.480	-167.42
3.8 GHz	0.895	145.14	2.63	15.23	0.019	-37.28	0.491	-170.27
4.0 GHz	0.895	141.81	2.50	10.94	0.018	-38.13	0.501	-173.18
4.2 GHz	0.895	138.42	2.39	6.64	0.018	-38.69	0.510	-176.16
4.4 GHz	0.896	134.95	2.29	2.32	0.017	-38.93	0.519	-179.20
4.6 GHz	0.896	131.39	2.20	-2.02	0.017	-38.84	0.526	177.68
4.8 GHz	0.896	127.73	2.12	-6.40	0.016	-38.43	0.533	174.48
5.0 GHz	0.895	123.96	2.05	-10.82	0.016	-37.69	0.539	171.19
5.2 GHz	0.895	120.07	1.99	-15.29	0.016	-36.68	0.545	167.80
5.4 GHz	0.895	116.05	1.93	-19.83	0.016	-35.43	0.549	164.31
5.6 GHz	0.895	111.90	1.87	-24.44	0.016	-34.05	0.553	160.70
5.8 GHz	0.895	107.59	1.82	-29.13	0.016	-32.64	0.556	156.95
6.0 GHz	0.895	103.14	1.78	-33.91	0.016	-31.32	0.559	153.06

To download the s-parameters in s2p format, go to the CGH27030 Product page.

Product Dimensions CGH27030F (Package Type — 440166)



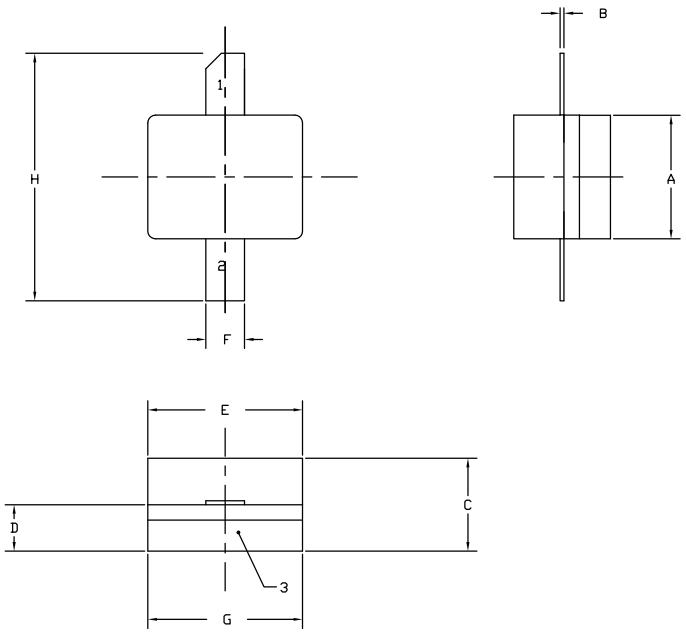
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	ø .100		2.54	
K	0.375		9.53	

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Dimensions CGH27030P (Package Type — 440196)



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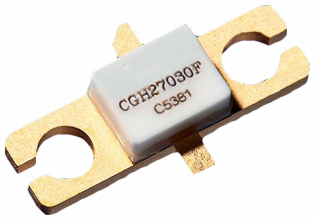
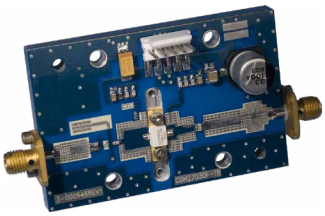
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.003	0.006	0.10	0.15
C	0.115	0.135	2.92	3.17
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.195	0.205	4.95	5.21
H	0.280	0.360	7.11	9.14

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH27030F	GaN HEMT	Each	
CGH27030P	GaN HEMT	Each	
CGH27030F-AMP	Test board with GaN HEMT installed	Each	

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